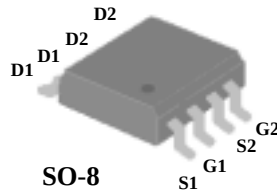




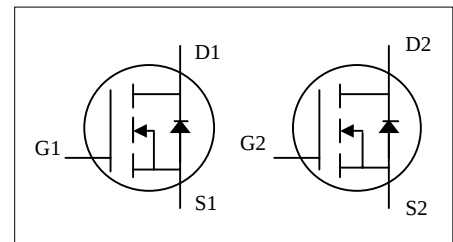
- ▼ Low Gate Charge
- ▼ Simple Drive Requirement
- ▼ Fast Switching



BV_{DS}	25V
$R_{DS(ON)}$	37m Ω
I_D	5.8A

Description

The Advanced Power MOSFETs from APEC provide the designer with the best combination of fast switching, ruggedized device design, ultra low on-resistance and cost-effectiveness.



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	25	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_A=25^\circ\text{C}$	Continuous Drain Current ³	5.8	A
$I_D@T_A=70^\circ\text{C}$	Continuous Drain Current ³	4.6	A
I_{DM}	Pulsed Drain Current ¹	30	A
$P_D@T_A=25^\circ\text{C}$	Total Power Dissipation	2	W
	Linear Derating Factor	0.016	W/ $^\circ\text{C}$
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

Thermal Data

Symbol	Parameter	Value	Unit
$R_{thj-amb}$	Thermal Resistance Junction-ambient ³ Max.	62.5	$^\circ\text{C}/\text{W}$


Electrical Characteristics@T_j=25°C(unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	25	-	-	V
ΔBV _{DSS} /ΔT _j	Breakdown Voltage Temperature Coefficient	Reference to 25°C, I _D =1mA	-	0.03	-	V/°C
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =10V, I _D =5A	-	-	37	mΩ
		V _{GS} =4.5V, I _D =3.5A	-	-	60	mΩ
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250uA	1	-	3	V
g _{fs}	Forward Transconductance	V _{DS} =10V, I _D =5A	-	6.5	-	S
I _{DSS}	Drain-Source Leakage Current (T _j =25°C)	V _{DS} =25V, V _{GS} =0V	-	-	1	uA
	Drain-Source Leakage Current (T _j =70°C)	V _{DS} =20V, V _{GS} =0V	-	-	25	uA
I _{GSS}	Gate-Source Leakage	V _{GS} = ± 20V	-	-	±100	nA
Q _g	Total Gate Charge ²	I _D =5A	-	6.9	-	nC
Q _{gs}	Gate-Source Charge	V _{DS} =16V	-	1.2	-	nC
Q _{gd}	Gate-Drain ("Miller") Charge	V _{GS} =5V	-	4.5	-	nC
t _{d(on)}	Turn-on Delay Time ²	V _{DS} =16V	-	6	-	ns
t _r	Rise Time	I _D =5A	-	17.5	-	ns
t _{d(off)}	Turn-off Delay Time	R _G =3.3Ω, V _{GS} =10V	-	14.5	-	ns
t _f	Fall Time	R _D =3.2Ω	-	5.5	-	ns
C _{iss}	Input Capacitance	V _{GS} =0V	-	218	-	pF
C _{oss}	Output Capacitance	V _{DS} =25V	-	155	-	pF
C _{rss}	Reverse Transfer Capacitance	f=1.0MHz	-	63	-	pF

Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
I _S	Continuous Source Current (Body Diode)	V _D =V _G =0V, V _S =1.2V	-	-	1.67	A
V _{SD}	Forward On Voltage ²	T _j =25°C, I _S =1.7A, V _{GS} =0V	-	-	1.2	V

Notes:

- 1.Pulse width limited by Max. junction temperature.
- 2.Pulse width ≤300us, duty cycle ≤2%.
- 3.Surface mounted on 1 in² copper pad of FR4 board; 135°C/W when mounted on Min. copper pad.

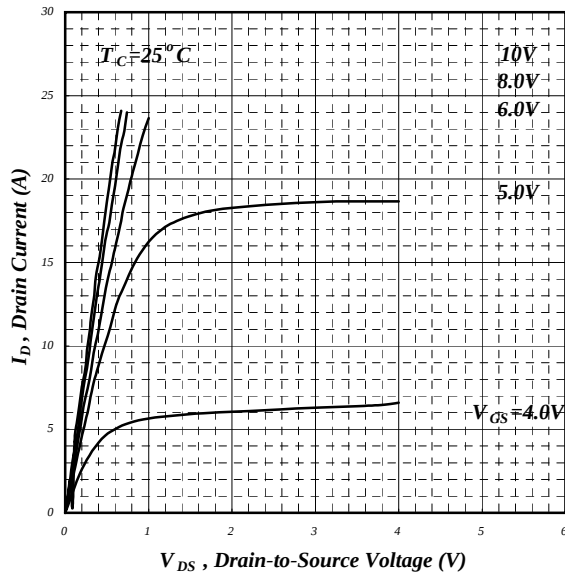


Fig 1. Typical Output Characteristics

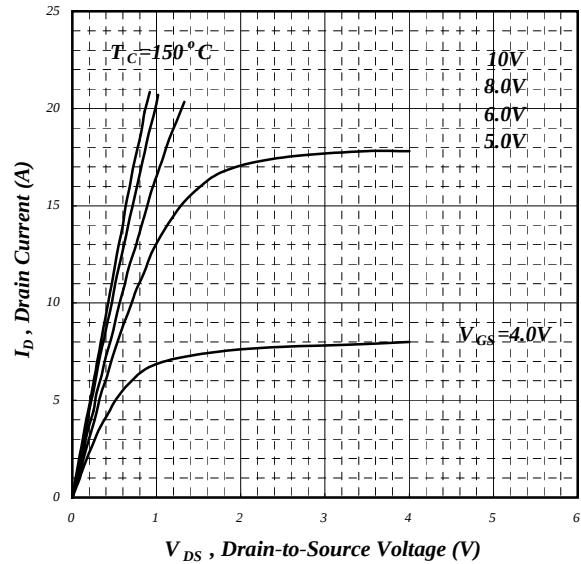


Fig 2. Typical Output Characteristics

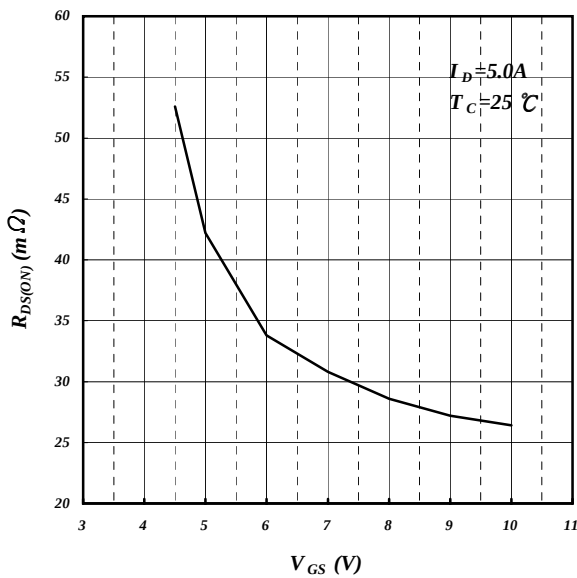


Fig 3. On-Resistance v.s. Gate Voltage

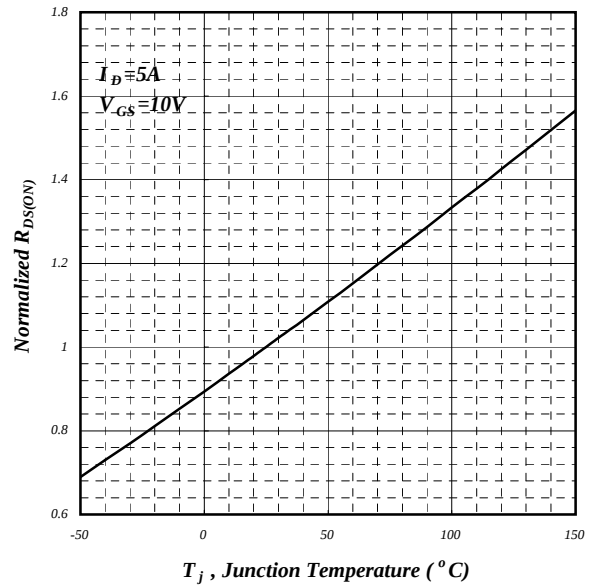


Fig 4. Normalized On-Resistance
v.s. Junction Temperature

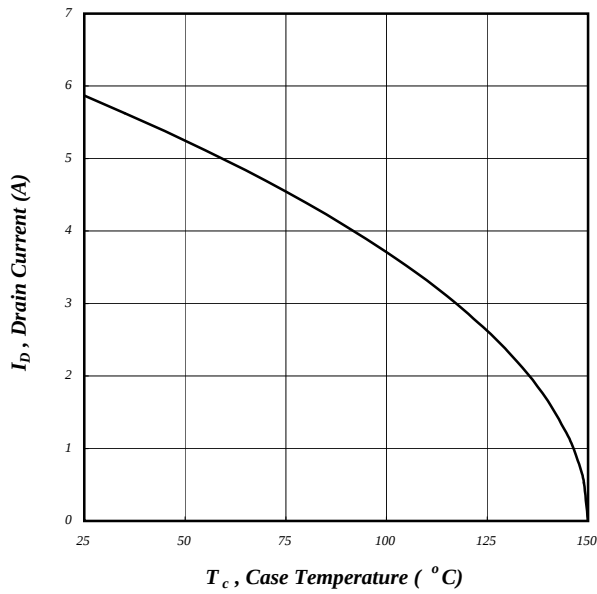


Fig 5. Maximum Drain Current v.s. Case Temperature

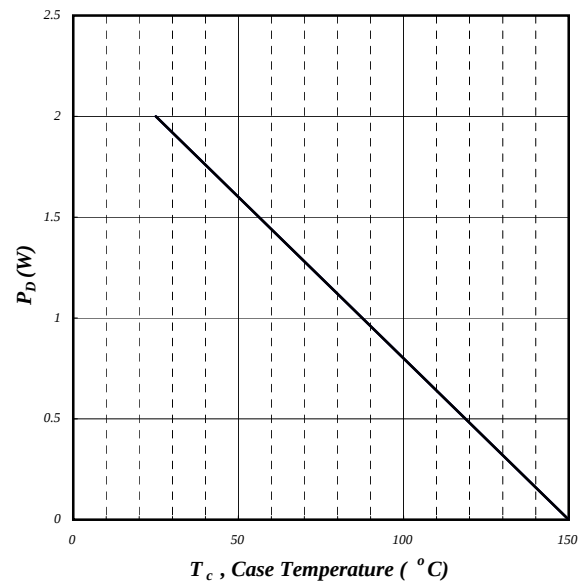


Fig 6. Typical Power Dissipation

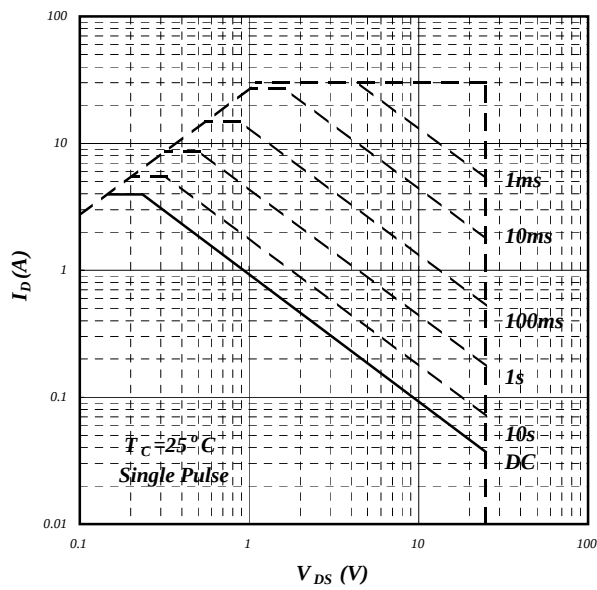


Fig 7. Maximum Safe Operating Area

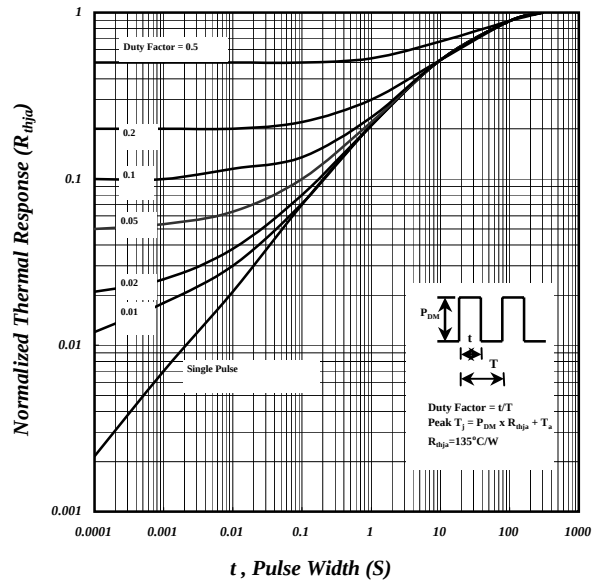


Fig 8. Effective Transient Thermal Impedance

